



Table 4.1

Parameter	Description	n-channel	p-channel	Units
V_{TH0}	Threshold voltage ($V_{BS}=0$)	0.7	-0.7	V
$K=\mu C_{OX}$	Transconductance Parameter (in saturation)	110	50	$\mu A/V^2$
γ	Bulk threshold parameter	0.4	0.57	
λ	Channel length modulation parameter	0.04(L=1 μm) 0.01(L=2 μm)	0.05(L=1 μm) 0.01(L=2 μm)	$V^{-1/2}$
$2 \Phi_F $	Surface potential at strong inversion	0.7	0.8	V

4.1 Calculate the output resistance and the minimum output voltage, while maintaining all devices in saturation, for the circuits shown in Figure 4.1. Assume that i_{OUT} is actually 10 μA . Use Table 4.1 for device model information.

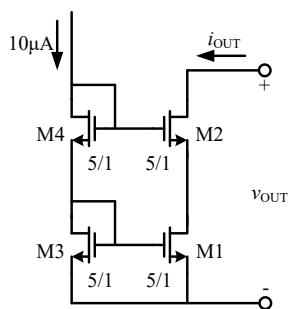


Fig 4.1

解:

$$V_{GS3} = V_{G3} = \sqrt{\frac{2i_D}{\beta}} + V_T = \sqrt{\frac{2 \times 10 \times 10^{-6}}{5 \times 110 \times 10^{-6}}} + 0.7 = \sqrt{\frac{20}{550}} + 0.7 = 0.891$$

$$V_{SB2} = V_{G3} = 0.891$$

$$V_{DS1} = V_{G3} + V_{GS4} - V_{GS2} \text{ because all devices are matched.}$$

$$g_{m2} = g_{m4} \cong \sqrt{(2K_n W/L)|I_D|} = \sqrt{2 \times 110 \times 10^{-6} \times 5/1 \times 10 \times 10^{-6}} = 104.9 \times 10^{-6}$$

$$g_{mbs2} = g_{mbs4} = g_{m2} \frac{\gamma}{2(2|\phi_F| + V_{SB})^{1/2}} = 104.9 \times 10^{-6} \frac{0.4}{2(0.7 + 0.891)^{1/2}} = 16.63 \times 10^{-6}$$

$$r_{out} = \frac{v_{out}}{i_{out}} = r_{ds1} + r_{ds2} + [(g_{m2} + g_{mbs2})r_{ds2}] r_{ds1}$$

$$g_{ds1} = g_{ds2} \cong I_D \lambda = 10 \times 10^{-6} \times 0.04 = 400 \times 10^{-9}$$

$$r_{ds1} = r_{ds2} = \frac{1}{g_{ds}} = 2.5 \times 10^6$$

$$r_{out} = 2.5 \times 10^6 + 2.5 \times 10^6 + [(104.9 \times 10^{-6} + 16.63 \times 10^{-6}) 2.5 \times 10^6] 2.5 \times 10^6$$

$$r_{out} = 764 \times 10^6$$

$$\begin{aligned} v_{out(min)} &= V_{GS3} + V_{GS4} - V_{T2} = V_{GS3} + \sqrt{\frac{2i_D}{\beta}} + V_{T4} - V_{T2} \\ &= V_{GS3} + \sqrt{\frac{2i_D}{\beta}} = 0.891 + \sqrt{\frac{2 \times 10 \times 10^{-6}}{5 \times 110 \times 10^{-6}}} = 1.082 \text{ V} \end{aligned}$$

4.2 In Fig. 4.2, assume that $(W/L)_1 = 50/0.5$, $\lambda = 0$, $I_{out} = 0.5 \text{ mA}$, $V_{DD} = 3 \text{ V}$ and M_1 is saturated.

(a) Determine R_2/R_1 .

(b) Calculate the sensitivity of I_{out} to V_{DD} , defined as $\partial I_{out}/\partial V_{DD}$ and normalized to I_{out} .

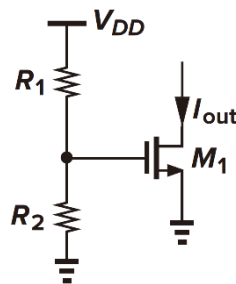


Fig 4.2

(a)

$$V_{GS} = \sqrt{\frac{2I_D}{K_n W/L}} + V_{TH} = 1 \text{ V} = V_{DD} \frac{R_2}{R_1 + R_2}$$

$$\frac{R_2}{R_1} = \frac{1}{2}$$

(b)

$$I_D = \frac{1}{2} K_n \frac{W}{L} \left(V_{DD} \frac{R_2}{R_1 + R_2} - V_{TH} \right)^2$$

$$\frac{\partial I_D}{\partial V_{DD}} = K_n \frac{W}{L} \left(V_{DD} \frac{R_2}{R_1 + R_2} - V_{TH} \right) \frac{R_2}{R_1 + R_2} = 1.1 \times 10^{-4}$$

$$\frac{\partial I_D}{\partial V_{DD}} / I_D = 2.2$$

4.3 Design M3 and M4 of Figure 4.3(a) so that the output characteristics are identical to the circuit shown in Figure 4.3(b). It is desired that i_{OUT} is ideally 10uA.

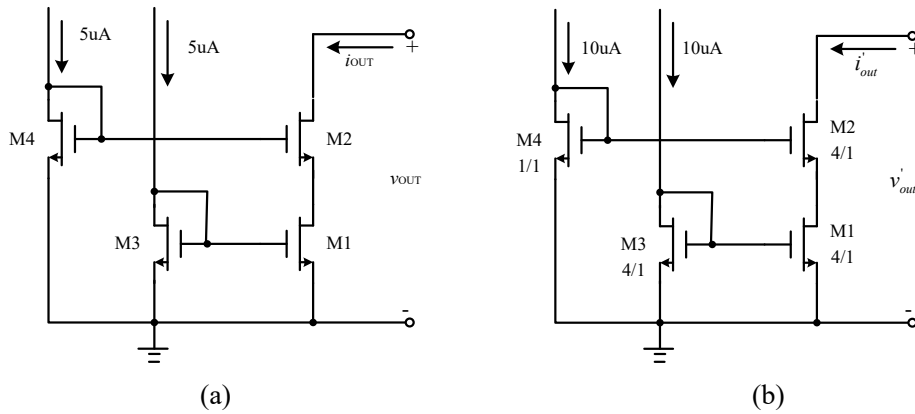


Figure 4.3

解:

For getting $i'_{out} = i_{out} = 10\mu A$

In Fig.4.2a), $\therefore i_3 = i_4 = 5\mu A$

Thus to ensure $i_{out} = 10\mu A$

We must have $\left(\frac{W}{L}\right)_1 = 2\left(\frac{W}{L}\right)_3$

$$\left(\frac{W}{L}\right)_3 = \frac{1}{2}\left(\frac{W}{L}\right)_1 = \frac{1}{2} \cdot \frac{4}{1} = \frac{2}{1}$$

In Fig. 4.2b) $i_4 = i_3 = i_1$

$$\left(\frac{W}{L}\right)_4 \Delta V_4^2 = \left(\frac{W}{L}\right)_1 \Delta V_1^2 \Rightarrow \left(\frac{1}{1}\right) \Delta V_4^2 = \left(\frac{4}{1}\right) \Delta V_1^2$$

$$\therefore \frac{\Delta V_4^2}{\Delta V_1^2} = \frac{4}{1} \Rightarrow \Delta V_4 = 2\Delta V_1$$

$$V_{G4} = V_T + 2\Delta V_1$$

$$V_{G2} = V_{G4} = V_T + 2\Delta V_1$$

$$\therefore V_{MIN} = 2\Delta V_1$$

And we get V_{MIN} in Fig.5.2(a): $V_{MIN} = 2\Delta V_1$

$$\therefore V_{G2} = V_{G4} = V_T + 2\Delta V_1 \quad \text{and} \quad \Delta V_4 = 2\Delta V_1$$

In Fig.5.2(a): $i_4 = i_3 = \frac{1}{2}i_1$

$$\left(\frac{W}{L}\right)_4 \Delta V_4^2 = \frac{1}{2} \left(\frac{W}{L}\right)_1 \Delta V_1^2$$

$$\left(\frac{W}{L}\right)_4 = \frac{1}{2} \left(\frac{W}{L}\right)_1 \left(\frac{\Delta V_1}{\Delta V_4}\right)^2$$

$$\text{For } \left(\frac{\Delta V_4}{\Delta V_1}\right)^2 = 4 \Rightarrow \left(\frac{\Delta V_1}{\Delta V_4}\right)^2 = \frac{1}{4}$$

$$\left(\frac{W}{L}\right)_4 = \frac{1}{8} \left(\frac{W}{L}\right)_1 = \frac{1}{8} \cdot \frac{4}{1} = \frac{1}{2}$$

4.4 Assume that W/L ratios of Figure 4.5 are $(W/L)_1 = 2\mu\text{m}/1\mu\text{m}$ and $(W/L)_2 = (W/L)_3 = (W/L)_4 = 1\mu\text{m}/1\mu\text{m}$. Find the dc value of v_{IN} that will give a dc current in M1 of $110\mu\text{A}$. Calculate the small signal voltage gain and output resistance using the parameters of Table 4.1. Assume $\lambda=\gamma=0$.

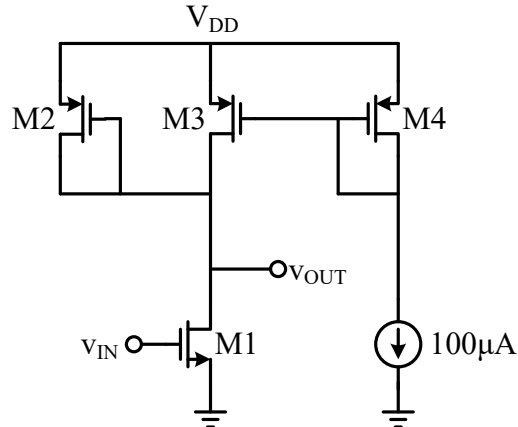


Figure 4.4

Solution:

$$I_{D1} = \frac{1}{2} K'_N \left(\frac{W}{L}\right)_1 (V_{in} - V_{TH1})^2$$

$$110\mu = \frac{1}{2} \times (110\mu) \times \frac{2}{1} \times (V_{in} - 0.7)^2$$

$$V_{in} = 1.7V$$

$$I_{D3} = I_{D4} = 100\mu A$$

$$I_{D2} = I_{D1} - I_{D3} = 10\mu A$$

$$A_v \cong -\frac{g_{m1}}{g_{m2}} = -\sqrt{\frac{K'_N (W/L)_1}{K'_P (W/L)_2} \frac{I_{D1}}{I_{D2}}} = -\sqrt{\frac{110\mu}{50\mu} \times \frac{2}{1} \times \frac{110\mu}{10\mu}} = -6.96V/V$$

$$R_{out} \cong \frac{1}{g_{m2}} = \frac{1}{\sqrt{2K'_P (W/L)_2 I_{D2}}} = \frac{1}{\sqrt{2 \times 50 \times 10^{-6} \times 1 \times 10 \times 10^{-6}}} = 31.6K\Omega$$